

2SD1297

Silicon NPN Transistors



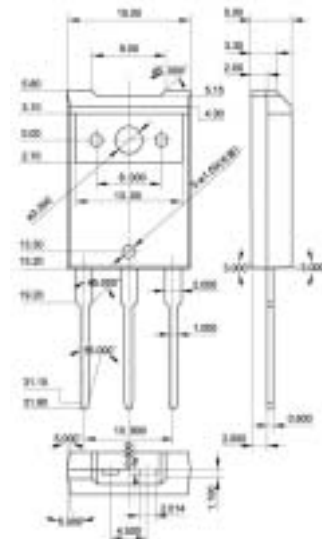
B C E

◆ Features

- Darlington
- With TO-3PFa package
- Low speed power switching applications

◆ Absolute Maximum Ratings Tc=25

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	150	V
V _{CEO}	Collector to emitter voltage	100	V
V _{EBO}	Emitter to base voltage	5	V
I _C	Collector current-Continuous	25	A
P _D	Total Power Dissipation@TC=25	100	W
T _j	Junction temperature	150	
T _{stg}	Storage temperature	-55~150	



TO-3PFa

◆ Electrical Characteristics Tc=25

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =100mA; I _B =0	100		V
V _{CBO}	Collector-Base Voltage				
I _{CEO}	Collector Cutoff Current				
I _{CBO}	Collector Cutoff Current	V _{CB} =100V; I _E =0		10	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} =5V; I _C =0		5	mA
V _{EBO}	Emitter-Base Voltage				
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =15A; I _B =0.03A		1.5	V
V _{CE(sat-2)}	Collector-emitter saturation voltages				
h _{FE-1}	Forward current transfer ratio	I _C =15A; V _{CE} =2V	1000	30000	
h _{FE-2}	Forward current transfer ratio				
V _{BE(sat)1}	Base-emitter saturation voltages	I _C =15A; I _B =0.03A		2.2	V
V _{BE(sat)2}	Base-emitter saturation voltages				
f _T	Transition frequency				